पेटेंट कार्यालय शासकीय जर्नल

OFFICIAL JOURNAL OF THE PATENT OFFICE

निर्गमन सं. 39/2020 ISSUE NO. 39/2020

शुक्रवार FRIDAY दिनांकः 25/09/2020

DATE: 25/09/2020

पेटेंट कार्यालय का एक प्रकाशन PUBLICATION OF THE PATENT OFFICE

(19) INDIA

(22) Date of filing of Application :09/09/2020

(43) Publication Date: 25/09/2020

(54) Title of the invention: SYSTEM AND METHOD FOR TRAFFIC CONTROL

(51) International classification	:G06N0003063000, G09F0027000000, G01S0011120000, G08G0001015000, G01S0013920000	(71)Name of Applicant: 1)CMR COLLEGE OF ENGINEERING & TECHNOLOGY Address of Applicant: CMR College of Engineering & Technology, Kandlakoya(V), Medchal Road, Hyderabad-501401, Telangana, India. Telangana India
(31) Priority Document No	:NA	2)K SAI CHARAN REDDY
(32) Priority Date	:NA	3)A.HARISH
(33) Name of priority country	:NA	4)K.SWAPNA
(86) International Application No	:NA	5)B. CHAKRADHAR
Filing Date	:NA	6)Dr.K.L.S SOUJANYA
(87) International Publication No	: NA	(72)Name of Inventor:
(61) Patent of Addition to ApplicationNumberFiling Date(62) Divisional to Application Number	:NA :NA :NA	1)Major Dr. V.A NARAYANA 2)K SAI CHARAN REDDY 3)A.HARISH 4)K.SWAPNA
Filing Date	:NA	5)B. CHAKRADHAR 6)Dr.K.L.S SOUJANYA

(57) Abstract:

Exemplary embodiment of the present disclosure is directed towards a system for traffic control with a spike barrier with spike strips to work upon the sound waves generated from vehicles passing at the proximity of the spike barrier and the sound frequency detector is housed on the signal pole with a RF transmitter and an RF receiver; a control board configured is mounted on the signal pole with a passive two-terminal resistor kit that implements electrical resistance as a circuit element and the resistors are fixed resistors and variable resistors; an open source hardware comprising of communications interfaces, including Universal Serial Bus (USB); a light emitting diode to emit light when current flows through it, and the color of the light (corresponding to the energy of the photons) is determined by the energy required for electrons to cross the band gap of the semiconductor. FIG 1

No. of Pages: 17 No. of Claims: 6